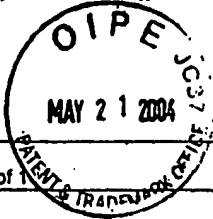


Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)



Complete if Known	
Application Number	10/721585
Filing Date	November 25, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2825-2891
Examiner Name	Unknown C. Everhart
Attorney Docket No: 1303.017US2	

Sheet 1 of 1

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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ³
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Complete if Known

Application Number	Unknown 10/721,585
Filing Date	Even Date Herewith 11/25/03
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2625 2891
Examiner Name	Unknown C. Evenhart

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Attorney Docket No: 1303.017US2

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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown 10/721,555
	Filing Date	Even Date Herewith 11/25/03
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2826 2891
	Examiner Name	Unknown C. Everhart
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